

CRYSTAL OSCILLATOR

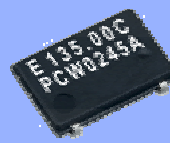
SPXO

SG-645 / SG-636 series

- Frequency range : 2.21675 MHz to 135 MHz
- Supply voltage : 2.5 V / 3.3 V / 5.0 V
- Function : Output enable(OE) or Standby(\overline{ST})
- Thickness : SG-645:1.5 mm Max.
SG-636:2.7 mm Max.



Product Number (please contact us)
 SG-645 : Q33645xx1xxxx00
 SG-636 : Q33636xx1xxxx00



Actual size

SG-645 series



SG-636 series



Specifications (characteristics)

| Item | Symbol | Specifications | | | | Remarks |
|---------------------------------------|-----------------------|---|---|---------------------------|---------------------------|---|
| | | SG-636 PTF | SG-636 PH | SG-636 PCE SG-636 SCE | SG-636 PDE | |
| Output frequency range | f_0 | 2.21675 MHz to 41.000 MHz | 41.001 MHz to 70.000 MHz | 2.21675 MHz to 40.000 MHz | 2.21675 MHz to 40.000 MHz | |
| Supply voltage | V _{cc} | 5.0 V \pm 0.5 V | | 3.3 V \pm 0.3 V | 2.5 V \pm 0.25 V | |
| Temperature range | Storage temperature | -55 °C to +100 °C | | | | Store as bare product after unpacking |
| | Operating temperature | -20 °C to +70 °C | | | | |
| Frequency tolerance | f_{tol} | C: \pm 100 \times 10 ⁻⁶ | | | | -20 °C to +70 °C |
| Current consumption | I _{cc} | 17 mA Max. | 35 mA Max. | 9 mA Max. | 5 mA Max. | No load condition |
| Disable current | I _{dis} | 10 mA Max. | 20 mA Max. | 5 mA Max. | 3 mA Max. | OE=GND |
| Stand-by current | I _{std} | — | | 2 μ A Max. | — | \overline{ST} =GND(SCE) |
| Symmetry | SYM | 40 % to 60 % | | 45 % to 55 % | | CMOS load:50 % V _{cc} level |
| | | 45 % to 55 % | — | | — | |
| High output voltage | V _{OH} | V _{cc} -0.4 V Min. | | | | I _{OH} =-8 mA(PTF)/-4 mA(PH,SCE,PCE), /-3.2 mA(PDE) |
| Low output voltage | V _{OL} | 0.4 V Max. | | | | I _{OL} =16 mA(PTF)/4mA(PH,SCE,PCE) /3.2 mA(PDE) |
| Output load condition (TTL) | L _{TTL} | 10 TTL Max. | — | | | L _{CMOS} \leq 15 pF |
| Output load condition (CMOS) | L _{CMOS} | 50 pF Max. | 20 pF Max.(\leq 55 MHz) 15 pF Max.($>$ 55 MHz) | 30 pF Max. | 15 pF Max. | |
| Output enable / disable input voltage | V _{IH} | 2.0 V Min. | | 80 % V _{cc} Min. | | OE Terminal or \overline{ST} Terminal (SCE) |
| | V _{IL} | 0.8 V Max. | | 20 % V _{cc} Max. | | |
| Rise time / Fall time | t_r / t_f | 7 ns Max. | | 5 ns Max. | | CMOS load:20 % V _{cc} to 80 % V _{cc} level |
| | | 5 ns Max. | | — | | TTL load:0.4 V to 2.4 V level |
| Start-up time | t_{str} | 4 ms Max. | 10 ms Max. | 4 ms Max. | | Time at minimum supply voltage to be 0 s |
| Frequency aging | f_{aging} | \pm 5 \times 10 ⁻⁶ / year Max. | | | | +25 °C, V _{cc} =5.0 V/3.3 V/2.5 V, First year |

Specifications (characteristics)

| Item | Symbol | Specifications | | | Remarks |
|---------------------------------------|-----------------------|--|-----------------------------|-----------------------------|--|
| | | SG-636 PTG | SG-636 PHG | SG-636 PCG SG-636 SCG | |
| Output frequency range | f_0 | 2.21675 MHz to 33.000 MHz *1 | | | |
| Supply voltage | V _{cc} | 4.5 V to 5.5 V | | 2.7 V to 3.6 V | |
| Temperature range | Storage temperature | -55 °C to +100 °C | | | Store as bare product after unpacking |
| | Operating temperature | -20 °C to +70 °C | | | |
| Frequency tolerance | f_{tol} | B: \pm 50 \times 10 ⁻⁶ C: \pm 100 \times 10 ⁻⁶ | | | -20 °C to +70 °C |
| Current consumption | I _{cc} | 25 mA Max. | | 12 mA Max. | No load condition |
| Disable current | I _{dis} | 20 mA Max. | | 10 mA Max. | OE=GND (PTG,PHG,PCG) |
| Stand-by current | I _{std} | — | | 50 μ A Max. | \overline{ST} =GND (SCG) |
| Symmetry | SYM | — | | 45 % to 55 % | 50 % V _{cc} level, L _{CMOS} =25 pF |
| | | 40 % to 60 % | — | | 1.4 V level, L _{CMOS} =25 pF |
| High output voltage | V _{OH} | 2.4 V Min. | — | V _{cc} -0.4 V Min. | I _{OH} =-8 mA |
| | | — | V _{cc} -0.4 V Min. | — | I _{OH} =-16 mA |
| Low output voltage | V _{OL} | — | | 0.4 V Max. | I _{OL} =8 mA |
| | | 0.4 V Max. | | — | — |
| Output load condition | L _{CMOS} | 25 pF Max. | | | |
| Output enable / disable input voltage | V _{IH} | 2.0 V Min. | | 70 % V _{cc} Min. | OE Terminal or \overline{ST} Terminal |
| | V _{IL} | 0.8 V Max. | | 20 % V _{cc} Max. | |
| Rise time / Fall time | t_r / t_f | — | 3.4 ns Max. | 4 ns Max. | 20 % V _{cc} to 80 % V _{cc} level, L _{CMOS} \leq 25 pF |
| | | 2.4 ns Max. | — | — | TTL load:0.4 V to 2.4 V level, L _{CMOS} \leq 25 pF |
| Start-up time | t_{str} | 12 ms Max. | | | t=0 at 90 % V _{cc} |
| Frequency aging | f_{aging} | \pm 5 \times 10 ⁻⁶ / year Max. | | | +25 °C, V _{cc} =5.0 V/ 3.3 V, First year |

*1 4.1250 MHz < f_0 < 4.4336 MHz, 8.2500 MHz < f_0 < 8.8672 MHz, 16.500 MHz < f_0 < 17.7344 MHz : Unavailable

Specifications (characteristics)

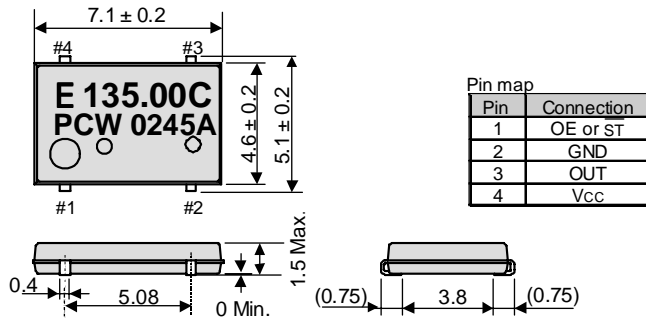
| Item | Symbol | Specifications | | | Remarks |
|---------------------------------------|------------------------------------|---|--------------------------------------|--------------------------------------|--|
| | | SG-636 PTW / STW SG-645 PTW / STW | SG-636 PHW / SHW SG-645 PHW / SHW | SG-636 PCW / SCW SG-645 PCW / SCW | |
| Output frequency range | f_0 | 32.001 MHz to 135.000 MHz | | | |
| Supply voltage | V_{cc} | 5.0 V \pm 0.5 V | | 3.3 V \pm 0.3 V | |
| Temperature range | Storage temperature T_{stg} | SG-636P ^{**} : -55 °C to +100 °C / SG-645P ^{**} : -55 °C to +125 °C | | | Store as bare product after unpacking |
| | Operating temperature T_{use} | -20 °C to +70 °C | | | |
| Frequency tolerance | f_{tol} | — | | M: $\pm 50 \times 10^{-6}$ | SG-645PCW / SCW Only |
| | | B: $\pm 50 \times 10^{-6}$ C: $\pm 100 \times 10^{-6}$ | | — | -20 °C to +70 °C *1 |
| Current consumption | I_{cc} | 45 mA Max. | | 28 mA Max. | No load condition(Max. frequency range) |
| Disable current | I_{dis} | 30 mA Max. | | 16 mA Max. | OE=GND (PTW,PHW,PCW) |
| Stand-by current | I_{std} | 50 μ A Max. | | | \overline{ST} =GND (STW,SHW,SCW) |
| Symmetry | SYM | — | | 40 % to 60 % | 50 % V_{cc} level, L_{CMOS} =Max. |
| | | 40 % to 60 % | | — | 1.4 V level, L_{CMOS} =Max. |
| High output voltage | V_{OH} | V_{cc} -0.4 V Min. | | | I_{OH} =-16 mA(PTW , STW , PHW , SHW) /-8 mA(PCW , SCW) |
| Low output voltage | V_{OL} | 0.4 V Max. | | | I_{OL} = 16 mA(PTW , STW , PHW , SHW) / 8 mA(PCW , SCW) |
| Output load condition (TTL) | L_{TTL} | 5 TTL Max. | — | — | $f_0 \leq 90$ MHz, Max.Supply voltage. |
| Output load condition (CMOS) | L_{CMOS} | 15 pF Max. | | | Max.frequency, Max.Supply voltage. |
| Output enable / disable input voltage | V_{IH} | 2.0 V Min. | | 70 % V_{cc} Min. | OE Terminal or \overline{ST} Terminal |
| | V_{IL} | 0.8 V Max. | | 20 % V_{cc} Max. | |
| Rise time / Fall time | t_r / t_f | — | | 4 ns Max. | 20 % V_{cc} to 80 % V_{cc} level, $L_{CMOS} \leq$ Max. |
| | | 4 ns Max. | | — | — |
| Start-up time | t_{str} | 10 ms Max. | | | Time at minimum supply voltage to be 0 s |
| Frequency aging | f_{aging} | $\pm 5 \times 10^{-6}$ / year Max. | | | +25 °C, V_{cc} =5.0 V / 3.3 V, First year |

*1 SG-636 series "C" tolerance : 40 MHz< f_0 <135 MHz

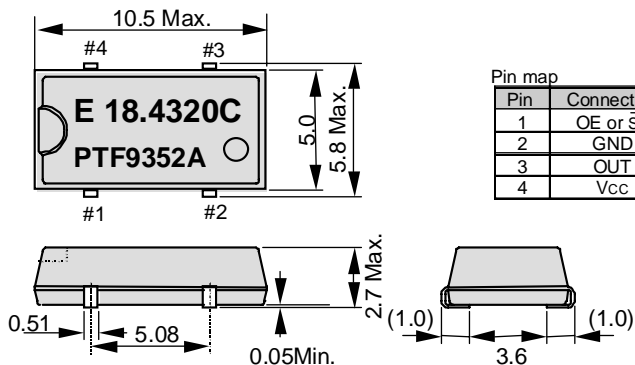
External dimensions

(Unit:mm)

● SG-645 series



● SG-636 series



Metal may be exposed on the top or bottom of this product.
This will not affect any quality, reliability or electrical spec.

Note.

OE pin (PTF,PH,PCE,PDE,PTW,PHW,PCW,PTG,PHG,PCG)

OE pin = "H" or "open" : Specified frequency output.

OE pin = "L" : Output is high impedance.

\overline{ST} pin (STW, SHW, SCW,SCG)

\overline{ST} pin = "H" or "open" : Specified frequency output.

\overline{ST} pin = "L" : Output is low level (weak pull - down), oscillation stops.

\overline{ST} pin (SCE)

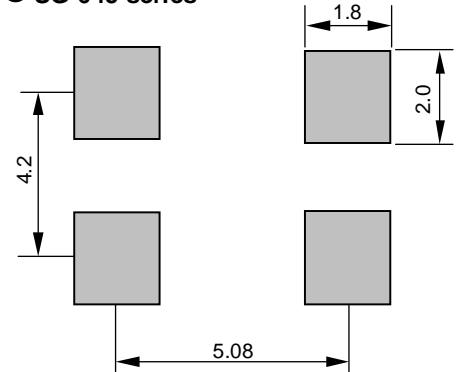
\overline{ST} pin = "H" or "open" : Specified frequency output.

\overline{ST} pin = "L" : Output is low level , oscillation stops.

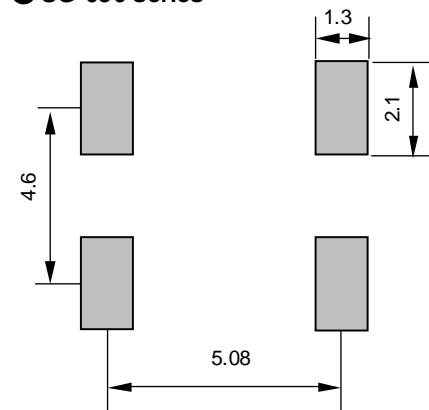
Footprint (Recommended)

(Unit:mm)

● SG-645 series



● SG-636 series



“QMEMS” EPSON TOYOCOM

In order to meet customer needs in a rapidly advancing digital, broadband and ubiquitous society, we are committed to offering products that are one step ahead of the market and a rank above the rest in quality. To achieve our goals, we follow a “3D (three device) strategy” designed to drive both horizontal and vertical growth. We will to grow our three device categories of “Timing Devices”, “Sensing Devices” and “Optical Devices”, and expand vertical growth through a combination of products from these categories.

A Quartz MEMS is any high added value quartz device that exploits the characteristics of quartz crystal material but that is produced using MEMS (micro-electro-mechanical system) processing technology.

Market needs are advancing faster than previously imagined toward smaller, more stable crystal products, but we will stay ahead of the curve by rolling out products that exceed market speed and quality requirements. We want to further accelerate the 3D strategy by QMEMS.

Quartz devices have become crucial in the network environment where products are increasingly intended for broadband, ubiquitous applications and where various types of terminals can transfer information almost immediately via LAN and WAN on a global scale. Epson Toyocom Corporation addresses every single aspect within a network environment. The new corporation offers “Digital Convergence” solutions to problems arising with products for consumer use, such as, core network systems and automotive systems.



PROMOTION OF ENVIRONMENTAL MANAGEMENT SYSTEM CONFORMING TO INTERNATIONAL STANDARDS

At Epson Toyocom, all environmental initiatives operate under the Plan-Do-Check-Action(PDCA) cycle designed to achieve continuous improvements. The environmental management system (EMS) operates under the ISO 14001 environmental management standard.

ISO 14000 is an international standard for environmental management that was established by the International Standards Organization in 1996 against the background of growing concern regarding global warming, destruction of the ozone layer and global deforestation

All of our major manufacturing and non-manufacturing sites, in Japan and overseas, completed the acquisition of ISO 14001 certification. In the future, new group companies will be expected to acquire the certification around the third year of operations.

WORKING FOR HIGH QUALITY

In order to provide high quality and reliable products and services than meet customer needs, Epson Toyocom made early efforts towards obtaining ISO9000 series certification and has acquired ISO9001 for all business establishments in Japan and abroad. We have also acquired ISO/TS 16949 certification that is requested strongly by major automotive manufacturers as standard.

QS-9000 is an enhanced standard for quality assurance systems formulated by leading U.S. automobile manufacturers based on the international ISO 9000 series.

ISO/TS 16949 is a global standard based on QS-9000, a severe standard corresponding to the requirements from the automobile industry.

► Explanation of the mark that are using it for the catalog

| | |
|--|---|
| | <ul style="list-style-type: none"> ► Pb free. ► Complies with EU RoHS directive. |
| | <ul style="list-style-type: none"> ► Pb free terminal designed. Contains Pb in products exempted by RoHS directive. (Contains Pb in sealing glass, high melting temperature type solder or other.) ► Complies with EU RoHS directive. |
| | <ul style="list-style-type: none"> ► The products have been designed for high reliability applications such as Automotive. |

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- These products are intended for general use in electronic equipment. When using them in specific applications that require extremely high reliability, such as the applications stated below, you must obtain permission from Epson Toyocom in advance.
 - / Space equipment (artificial satellites, rockets, etc.) / Transportation vehicles and related (automobiles, aircraft, trains, vessels, etc.)
 - / Medical instruments to sustain life / Submarine transmitters / Power stations and related / Fire work equipment and security equipment
 - / traffic control equipment / and others requiring equivalent reliability.
- In this new crystal master for Epson Toyocom, product codes and markings will remain as previously identified prior to the merger. Due to the on-going strategy of gradual unification of part numbers, please review product codes and markings, as they will change during the course of the coming months.

We apologize for the inconvenience, but we will eventually have a unified part numbering system for Epson Toyocom that will be user friendly.